

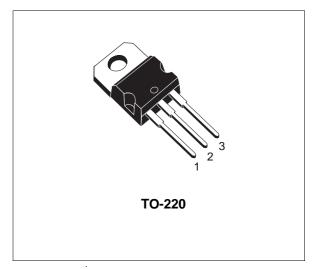
MJE2955T MJE3055T

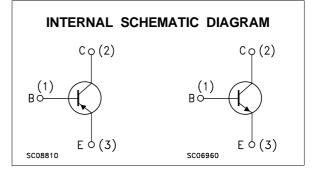
COMPLEMENTARY SILICON POWER TRANSISTORS

- STMicroelectronics PREFERRED SALESTYPES
- COMPLEMENTARY PNP NPN DEVICES

DESCRIPTION

The MJE3055T is a silicon Epitaxial-Base NPN transistor in Jedec TO-220 package. It is intended for power switching circuits and general-purpose amplifiers. The complementary PNP type is MJE2955T.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
	N		MJE3055T	
		PNP	MJE2955T	
Vceo	Collector-Emitter Voltage ($I_B = 0$)		60	V
Vсво	Collector-Base Voltage ($I_E = 0$)		70	V
V _{EBO}	Emitter-Base Voltage $(I_C = 0)$		5	V
Ι _C	Collector Current		10	А
Ι _Β	Base Current		6	А
Ptot	Total Power Dissipation at $T_{case} \le 25$ °C		75	W
T _{stg}	Storage Temperature		-55 to 150	°C
Ti	Max. Operating Junction Temperature		150	°C

For PNP types voltage and current values are negative.

THERMAL DATA

R _{thj-case} Thermal Resistance Junction-case	Max	1.66	°C/W
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ELECTRICAL CHARACTERISTICS ($T_{case} = 25 \, {}^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
I _{CEO}	Collector Cut-off Current (I _B = 0)	V _{CE} = 30 V				700	μA
I _{CEX}	Collector Cut-off Current (V _{BE} = 1.5V)	V _{CE} = 70 V T _{case =} 150°C				1 5	mA mA
I _{CBO}	Collector Cut-off Current (I _E = 0)	$V_{CBO} = 70 V$ $T_{case} = 150^{\circ}C$				1 10	mA mA
I _{EBO}	Emitter Cut-off Current $(I_C = 0)$	V _{EBO} = 5 V				5	mA
$V_{CEO(sus)^*}$	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 200 mA		60			V
V _{CE(sat)} *	Collector-Emitter Sustaining Voltage	$I_{C} = 4 A$ $I_{C} = 10 A$	I _B = 0.4 A I _B = 3.3 A			1.1 8	V V
V _{BE(on)} *	Base-Emitter on Voltage	I _C = 4 A	$V_{CE} = 4 V$			1.8	V
h _{FE}	DC Current Gain	$I_{C} = 4 A$ $I_{C} = 10 A$	V _{CE} = 4 V V _{CE} = 4 V	20 5		70	
f _T	Transistor Frequency	l _C = 500 mA f = 500 KHz	V _{CE} = 10 V	2			MHz

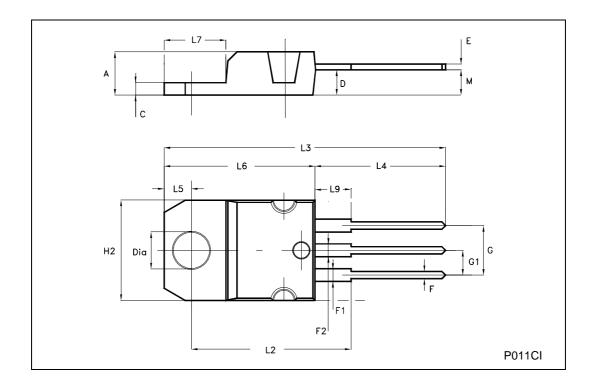
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* Pulsed: Pulse duration = $300\mu s$, duty cycle $\leq 2\%$ For PNP type voltage and current values are negative.

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DIM.		mm			inch	
DINI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	4.40		4.60	0.173		0.181
С	1.23		1.32	0.048		0.052
D	2.40		2.72	0.094		0.107
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.202
G1	2.40		2.70	0.094		0.106
H2	10.00		10.40	0.394		0.409
L2		16.40			0.645	
L4	13.00		14.00	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.20		6.60	0.244		0.260
L9	3.50		3.93	0.137		0.154
М		2.60			0.102	
DIA.	3.75		3.85	0.147		0.151

TO-220 MECHANICAL DATA



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